

Chan Shan

List of Publications by Year in descending order

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Version: 2024-02-01

11
papers

126
citations

1874746

5
h-index

1526636

10
g-index

12
all docs

12
docs citations

12
times ranked

151
citing authors

#	ARTICLE	IF	CITATIONS
1	In-Built N+ Pocket Electrically Doped Tunnel FET With Improved DC and Analog/RF Performance. <i>Micromachines</i> , 2020, 11, 960.	1.4	5
2	3D Numerical Simulation of a Z Gate Layout MOSFET for Radiation Tolerance. <i>Micromachines</i> , 2018, 9, 659.	1.4	9
3	Negative bias temperature instability in SOI-like p-type metal oxide semiconductor devices. <i>Micro and Nano Letters</i> , 2018, 13, 1151-1154.	0.6	0
4	Reliability improvements in SOI-like MOSFET with ESD and self-heating effect. <i>Micro and Nano Letters</i> , 2018, 13, 1649-1652.	0.6	4
5	A high-performance channel engineered charge-plasma-based MOSFET with high- \hat{n}° spacer. <i>Superlattices and Microstructures</i> , 2017, 112, 499-506.	1.4	4
6	A Low Turn-Off Loss 4H-SiC Trench IGBT With Schottky Contact in the Collector Side. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 4575-4580.	1.6	13
7	Graded-channel junctionless dual-gate MOSFETs for radiation tolerance. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 124201.	0.8	5
8	A Charge-Plasma-Based Transistor With Induced Graded Channel for Enhanced Analog Performance. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 2275-2281.	1.6	47
9	Improved performance of nanoscale junctionless transistor based on gate engineering approach. <i>Microelectronics Reliability</i> , 2015, 55, 318-325.	0.9	27
10	A Simulation Study of Hot Carrier Effects in Sol-Like Bulk Silicon nMOS Device. <i>IEEE Transactions on Electron Devices</i> , 2015, 62, 23-27.	1.6	5
11	A Simulation Study of Sol-Like Bulk Silicon MOSFET With Improved Performance. <i>IEEE Transactions on Electron Devices</i> , 2014, 61, 3339-3344.	1.6	7